Industrial Inductive Load Driver

This micro-integrated part provides a single component solution to switch inductive loads such as relays, solenoids, and small DC motors without the need of a free-wheeling diode. It accepts logic level inputs, thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

Features

- Provides Robust Interface between D.C. Relay Coils and Sensitive Logic
- Capable of Driving Relay Coils Rated up to 150 mA at 12 V, 24 V or 48 V
- Replaces 3 or 4 Discrete Components for Lower Cost
- Internal Zener Eliminates Need for Free-Wheeling Diode
- Meets Load Dump and other Automotive Specs
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Typical Applications

- Automotive and Industrial Environment
- Drives Window, Latch, Door, and Antenna Relays

Benefits

- Reduced PCB Space
- Standardized Driver for Wide Range of Relays
- Simplifies Circuit Design and PCB Layout
- Compliance with Automotive Specifications



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MARKING DIAGRAMS



SOT-23 CASE 318 STYLE 21



JW8 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)



SC-74 CASE 318F STYLE 7



JW8 = Specific Device Code

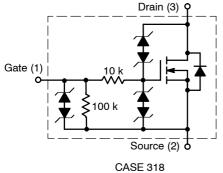
M = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NUD3160LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SZNUD3160LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NUD3160DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel
SZNUD3160DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



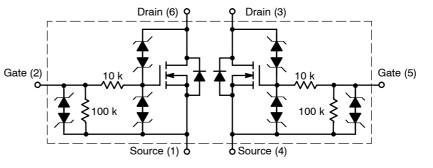


Figure 1. Internal Circuit Diagrams

$\textbf{MAXIMUM RATINGS} \ (T_J = 25^{\circ}C \ unless \ otherwise \ specified)$

Symbol	Rating	Value	Unit V	
V _{DSS}	Drain-to-Source Voltage - Continuous (T _J = 125°C)	60		
V_{GSS}	Gate-to-Source Voltage - Continuous (T _J = 125°C)	12	V	
I _D	Drain Current – Continuous (T _J = 125°C) Minimum copper, double sided board, T _A = 80°C SOT-23 SC74 Single device driven SC74 Both devices driven 1 in ² copper, double sided board, T _A = 25°C SOT-23 SC74 Single device driven SC74 Both devices driven	158 157 132 ea 272 263 230 ea	mA	
E _Z	Single Pulse Drain-to-Source Avalanche Energy (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T _J Initial = 85°C)	200	mJ	
P _{PK}	Peak Power Dissipation, Drain-to-Source (Notes 1 and 2) (T _J Initial = 85°C)	20	W	
E _{LD1}	Load Dump Pulse, Drain-to-Source (Note 3) $R_{SOURCE} = 0.5~\Omega,~T = 300~ms) \\ (For Relay's Coils/Inductive Loads of 80~\Omega or Higher)~(T_J Initial = ~85°C)$	60	V	
E _{LD2}	Inductive Switching Transient 1, Drain–to–Source (Waveform: R_{SOURCE} = 10 Ω , T = 2.0 ms) (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T _J Initial = 85°C)	100	V	
E _{LD3}	Inductive Switching Transient 2, Drain–to–Source (Waveform: R_{SOURCE} = 4.0 Ω , T = 50 μ s) (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T _J Initial = 85°C)	300	V	
Rev-Bat	Reverse Battery, 10 Minutes (Drain-to-Source) (For Relay's Coils/Inductive Loads of 80 Ω or more)	-14	V	
Dual-Volt	Dual Voltage Jump Start, 10 Minutes (Drain-to-Source)	28	V	
ESD	Human Body Model (HBM) According to EIA/JESD22/A114 Specification	2000	V	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Symbol	Rating	Value	Unit	
T _A	Operating Ambient Temperature		-40 to 125	°C
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-65 to 150	°C
P _D	Total Power Dissipation (Note 4) SO Derating above 25°C	T-23	225 1.8	mW mW/°C
P _D	Total Power Dissipation (Note 4) S Derating above 25°C	C-74	380 3.0	mW mW/°C
$R_{ hetaJA}$	SC-74 One Device Pov SC-74 Both Devices Equally Pov	vered 0T-23 vered	556 556 398 395 420 270	°C/W

Nonrepetitive current square pulse 1.0 ms duration.
 For different square pulse durations, see Figure 12.
 Nonrepetitive load dump pulse per Figure 3.
 Mounted onto minimum pad board.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	•		
Drain to Source Sustaining Voltage (I _D = 10 mA)	V _{BRDSS}	61	66	70	V
Drain to Source Leakage Current $ (V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}) \\ (V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 125^{\circ}\text{C}) \\ (V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}) \\ (V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 125^{\circ}\text{C}) $	I _{DSS}	- - - -	- - - -	0.5 1.0 50 80	μΑ
Gate Body Leakage Current $ (V_{GS} = 3.0 \text{ V}, V_{DS} = 0 \text{ V}) \\ (V_{GS} = 3.0 \text{ V}, V_{DS} = 0 \text{ V}, T_{J} = 125^{\circ}\text{C}) \\ (V_{GS} = 5.0 \text{ V}, V_{DS} = 0 \text{ V}) \\ (V_{GS} = 5.0 \text{ V}, V_{DS} = 0 \text{ V}, T_{J} = 125^{\circ}\text{C}) $	I _{GSS}	- - - -	- - - -	60 80 90 110	μΑ
ON CHARACTERISTICS					
Gate Threshold Voltage $ (V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}) $ $ (V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}, T_J = 125^{\circ}\text{C}) $	V _{GS(th)}	1.3 1.3	1.8 -	2.0 2.0	V
Drain to Source On–Resistance $ \begin{aligned} &(I_D=150 \text{ mA}, V_{GS}=3.0 \text{ V}) \\ &(I_D=150 \text{ mA}, V_{GS}=3.0 \text{ V}, T_J=125^\circ\text{C}) \\ &(I_D=150 \text{ mA}, V_{GS}=5.0 \text{ V}) \\ &(I_D=150 \text{ mA}, V_{GS}=5.0 \text{ V}, T_J=125^\circ\text{C}) \end{aligned} $	R _{DS(on)}	- - -	- - -	2.4 3.7 1.8 2.9	Ω
Output Continuous Current $(V_{DS} = 0.3 \text{ V}, V_{GS} = 5.0 \text{ V})$ $(V_{DS} = 0.3 \text{ V}, V_{GS} = 5.0 \text{ V}, T_{J} = 125^{\circ}\text{C})$	I _{DS(on)}	150 100	200 -	- -	mA
Forward Transconductance $(V_{DS} = 12 \text{ V}, I_D = 150 \text{ mA})$	9FS	_	400	-	mmho
DYNAMIC CHARACTERISTICS					
Input Capacitance $(V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, f = 10 \text{ kHz})$	C _{iss}	_	30	-	pf
Output Capacitance $(V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, f = 10 \text{ kHz})$	C _{oss}	_	14	-	pf
Transfer Capacitance $(V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, f = 10 \text{ kHz})$	C _{rss}	_	6.0	-	pf
SWITCHING CHARACTERISTICS					
Propagation Delay Times: High to Low Propagation Delay; Figure 2, $(V_{DS} = 12 \text{ V}, V_{GS} = 3.0 \text{ V})$ Low to High Propagation Delay; Figure 2, $(V_{DS} = 12 \text{ V}, V_{GS} = 3.0 \text{ V})$	t _{PHL} t _{PLH}	- -	918 798	_ _	ns
High to Low Propagation Delay; Figure 2, (V_{DS} = 12 V, V_{GS} = 5.0 V) Low to High Propagation Delay; Figure 2, (V_{DS} = 12 V, V_{GS} = 5.0 V)	t _{PHL} t _{PLH}	_ _	331 1160	- -	
Transition Times: Fall Time; Figure 2, (V_{DS} = 12 V, V_{GS} = 3.0 V) Rise Time; Figure 2, (V_{DS} = 12 V, V_{GS} = 3.0 V)	t _f t _r	- -	2290 618	-	ns
Fall Time; Figure 2, $(V_{DS} = 12 \text{ V}, V_{GS} = 5.0 \text{ V})$ Rise Time; Figure 2, $(V_{DS} = 12 \text{ V}, V_{GS} = 5.0 \text{ V})$	t _f t _r	_ _	622 600	- -	

TYPICAL WAVEFORMS

(T_J = 25°C unless otherwise specified)

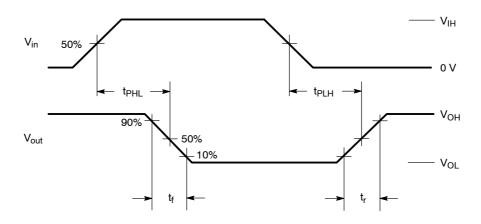


Figure 2. Switching Waveforms

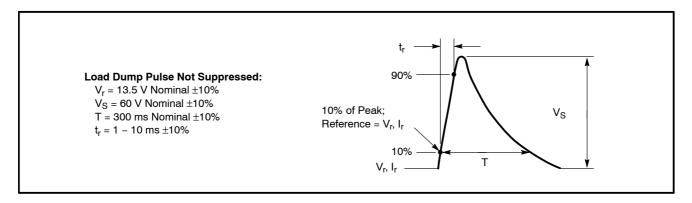
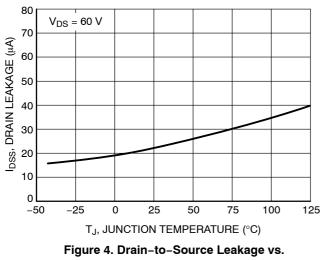


Figure 3. Load Dump Waveform Definition

TYPICAL PERFORMANCE CURVES

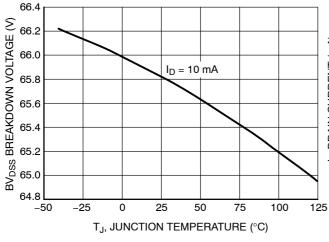
(T_J = 25°C unless otherwise specified)



80 I_{GSS} GATE LEAKAGE (µA) 60 $V_{GS} = 5 V$ 50 40 $V_{GS} = 3 V$ 30 20 -25 -50 25 50 100 125 T.J., JUNCTION TEMPERATURE (°C)

Junction Temperature

Figure 5. Gate-to-Source Leakage vs. **Junction Temperature**



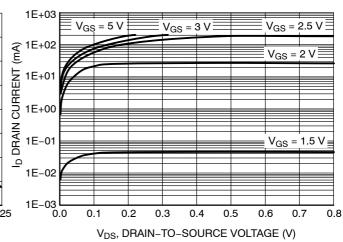
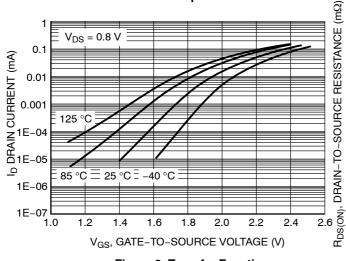


Figure 6. Breakdown Voltage vs. **Junction Temperature**

Figure 7. Output Characteristics



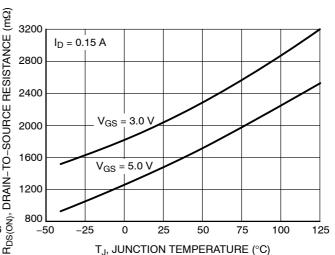


Figure 8. Transfer Function

Figure 9. On Resistance Variation vs **Junction Temperature**

TYPICAL PERFORMANCE CURVES

(T_J = 25°C unless otherwise specified)

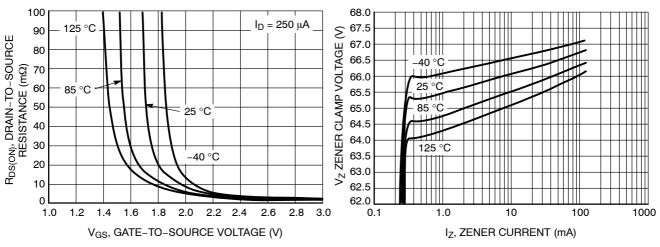


Figure 10. On Resistance Variation vs. Gate-to-Source Voltage

Figure 11. Zener Clamp Voltage vs. Zener Current

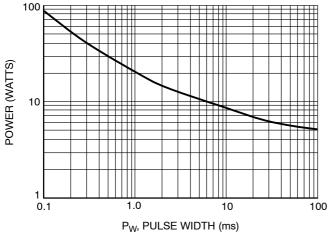


Figure 12. Maximum Non-repetitive Surge Power vs. Pulse Width

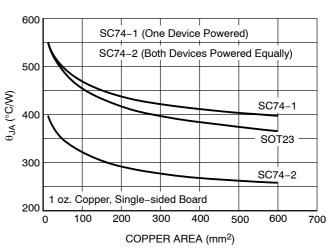


Figure 13. Thermal Performance vs. Board Copper Area

APPLICATIONS INFORMATION

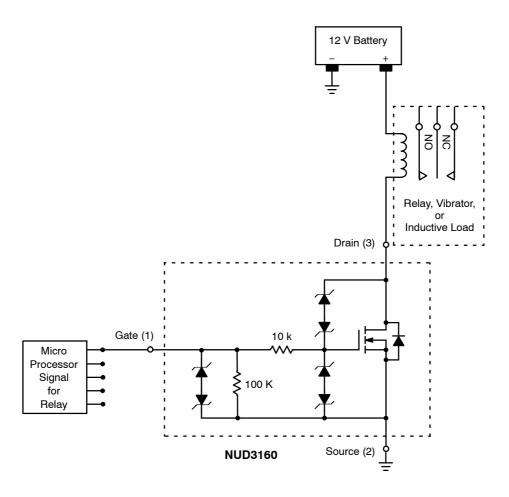
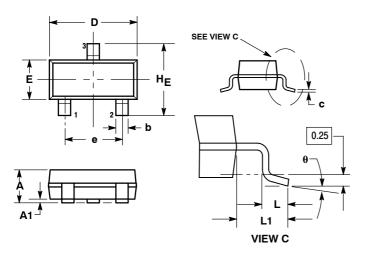


Figure 14. Applications Diagram

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

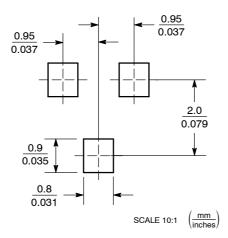
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	М	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.018	0.020	
С	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.081	
L	0.10	0.20	0.30	0.004	0.008	0.012	
L1	0.35	0.54	0.69	0.014	0.021	0.029	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
A	U _o		10°	O۰		10°	

STYLE 21:

PIN 1. GATE 2. SOURCE 3. DRAIN

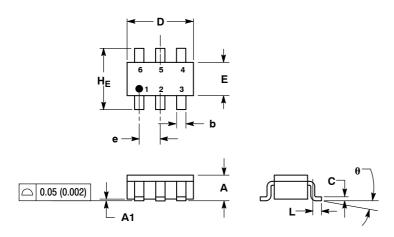
SOLDERING FOOTPRINT*



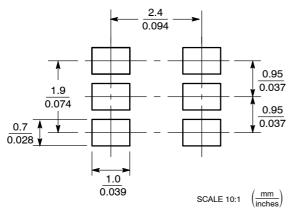
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SC-74 CASE 318F-05 ISSUE M



SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN NOM MA			
Α	0.90	1.00	1.10	0.035	0.039	0.043	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.25	0.37	0.50	0.010	0.015	0.020	
С	0.10	0.18	0.26	0.004	0.007	0.010	
D	2.90	3.00	3.10	0.114	0.118	0.122	
Е	1.30	1.50	1.70	0.051	0.059	0.067	
е	0.85	0.95	1.05	0.034	0.037	0.041	
L	0.20	0.40	0.60	0.008	0.016	0.024	
HE	2.50	2.75	3.00	0.099	0.108	0.118	
A	O°	_	10°	O°		10°	

STYLE 7:

PIN 1. 2. SOURCE 1 GATE 1

- DRAIN 2
- 4. SOURCE 2
- GATE 2
- 5. GATE 2 6. DRAIN 1

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